

# NPN SILICON RF POWER TRANSISTOR

**DESCRIPTION:**

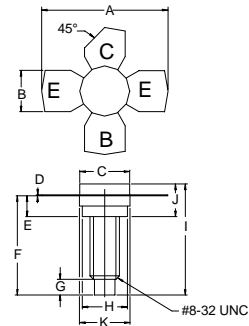
The **ASI MLN1027S** is Designed for Class A, Linear Applications up to 1.0 GHz.

**FEATURES:**

- Class A Operation
- $P_G = 9.0$  dB at 0.5 W/1.0 GHz
- **Omnigold™** Metalization System

**MAXIMUM RATINGS**

$I_C$	0.250 A
$V_{CB0}$	40 V
$V_{CEO}$	28 V
$V_{EBO}$	3.5 V
$P_{DISS}$	7.0 W @ $T_C = 25$ °C
$T_J$	-65 °C to +200 °C
$T_{STG}$	-65 °C to +150 °C
$\theta_{JC}$	25 °C/W

**PACKAGE STYLE .280 4L STUD**


DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	1.010 / 25.65	1.055 / 26.80
B	.220 / 5.59	.230 / 5.84
C	.270 / 6.86	.285 / 7.24
D	.003 / 0.08	.007 / 0.18
E	.117 / 2.97	.137 / 3.48
F		.572 / 14.53
G		.130 / 3.30
H	.245 / 6.22	.255 / 6.48
I		.640 / 16.26
J	.175 / 4.45	.217 / 5.51
K	.275 / 6.99	.285 / 7.24

**ORDER CODE: ASI10619**
**CHARACTERISTICS**  $T_C = 25$  °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
$BV_{CB0}$	$I_C = 1.0$ mA	40			V
$BV_{CEO}$	$I_C = 1.0$ mA	28			V
$BV_{EBO}$	$I_E = 1.0$ mA	3.5			V
$I_{CB0}$	$V_{CB} = 24$ V			0.5	mA
$h_{FE}$	$V_{CE} = 5.0$ V $I_C = 100$ mA	20		120	---
$C_{OB}$	$V_{CB} = 28$ V $f = 1.0$ MHz			3.5	pF
$P_G$	$V_{CE} = 20$ V $I_{CQ} = 100$ mA $f = 1.0$ GHz $P_{OUT} = 0.5$ W	9.0			dB